ABSTRACT OF THE DISCLOSURE

With a method according to the invention, an SOI substrate having on the surface thereof a single crystal silicon film formed on an insulator is heat-treated in a hydrogen-containing reducing atmosphere in order to smooth the surface and reduce the boron concentration without damaging the film thickness uniformity in a single wafer and among different wafers. The method is characterized in that the single crystal silicon film is arranged opposite to a member of non-oxidized silicon for heat treatment.

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